

**C1030-30**

Near Infrared LED CHIP

<Specifications>

Commodity Type and Physical Characteristics	
Material	InGaAsP/InP(DDH)
Top Side P(anode)side	Au Alloy
Bottom Side N(cathode)side	Au Alloy
Electrode Pattern	Fig.1
Chip Size	Fig.2
Chip Thickness	Fig.2
Emission Area	Fig.2

Electro-Optical Characteristics [Ta=25°C]						
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	IF=20mA		1.10	1.30	V
		IF=50mA		1.15	1.35	
Reverse Current	IR	VR=3V			10	uA
Power Intensity*	PO	IF=20mA		1.2		mW
		IF=50mA		2.8		
Peak Wavelength	$\lambda P$	IF=50mA		1030		nm
Spectral Radiation Bandwidth	$\Delta\lambda$	IF=50mA		50		nm
Centroid Wavelength	$\lambda C$	IF=50mA		1025		nm
Rise Time	tr	IF=50mA		20		ns
Fall Time	tf	IF=50mA		20		ns

Die shall be mounted on TO-18 gold header without resin coated.

\* Measured by PD G8370-85

[Unit:um]

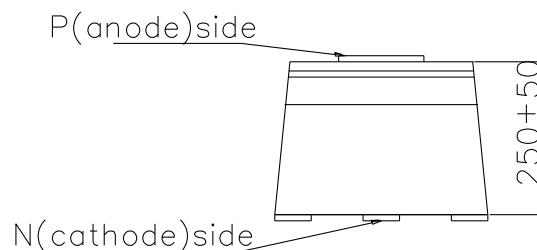
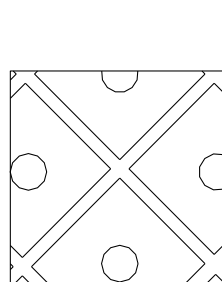
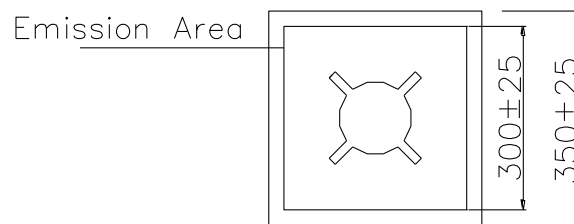
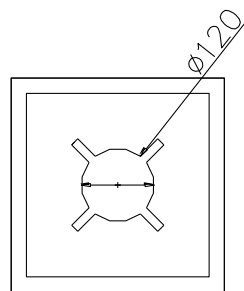


Fig.1 Electrode Pattern

Fig.2 Chip Size and Emission Area